Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

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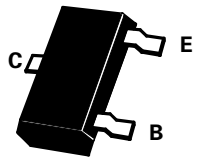
SOT23 PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

FMMTA92

ISSUE 4 - MARCH 2001 ✪

PARTMARKING DETAILS: – FMMTA92 - 4E
– FMMTA92R - 8E

COMPLEMENTARY TYPES: – FMMTA92 - FMMTA42



SOT23

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	FMMTA92	UNIT
Collector-Base Voltage	V_{CBO}	-300	V
Collector-Emitter Voltage	V_{CEO}	-300	V
Emitter-Base Voltage	V_{EBO}	-5	V
Continuous Collector Current	I_C	-200	mA
Power Dissipation at T_{amb}= 25°C	P_{tot}	330	mW
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

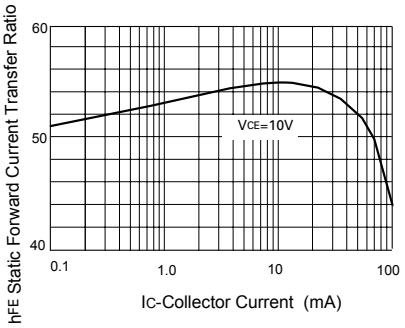
PARAMETER	SYMBOL	FMMTA92 MIN.	FMMTA92 MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-300		V	I_C=-100μA, I_E=0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-300		V	I_C=-1mA, I_B=0*
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		V	I_E=-100μA, I_C=0
Collector Cut-Off Current	I_{CBO}		-0.25 μA	μA μA	V_{CB}=-200V, I_E=0 V_{CB}=-160V, I_E=0-
Emitter Cut-Off Current	I_{EBO}		-0.1	μA	V_{EB}=-3V, I_E=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.5	V	I_C=-20mA, I_B=-2mA*
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-0.9	V	I_C=-20mA, I_B=-2mA*
Static Forward Current Transfer Ratio	h_{FE}	25 40 25			I_C=-1mA, V_{CE}=10V* I_C=-10mA, V_{CE}=10V* I_C=-30mA,V_{CE}=-10V*
Transition Frequency	f_T	50		MHz	I_C=-10mA, V_{CE}=-20V f=20MHz
Output Capacitance	C_{obo}		6	pF	V_{CB}=-20V, f=1MHz

*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤2%

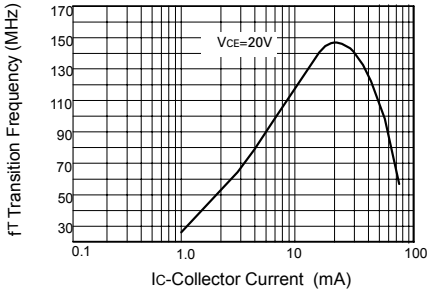
ZETEX

FMMTA92

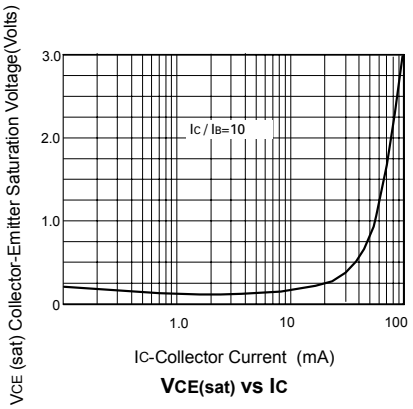
TYPICAL CHARACTERISTICS



hFE v IC



fT vs IC



VCE(sat) vs IC